

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO 107317-00039	SERIAL NO Div. of 08/787,451
LIST OF REFERENCES CITED BY APPLICANT  (Use several sheets if necessary)		APPLICANT HASHIMOTO et al.	
		FILING DATE Herewith	GROUP 2823

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
K.N.	AA	4,563,367	1/7/86	SHERMAN	156	643	
K.N.	AB	4,564,997	1/21/86	MATSUO ET AL.	156	647	
K.N.	AC	5,016,564	5/21/91	NAKAMURA ET AL.	156	345	
K.N.	AD	4,960,073	10/2/90	SUZUKI ET AL.	156	345	
K.N.	AE	5,022,977	6/11/91	MATSUOKA ET AL.			
K.N.	AF	5,259,922	11/9/93	YAMMNO ET AL.	156	643	

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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO PART.		
K.N.	AG	5-90224	4/9/93	JAPAN					
K.N.	AH	60/117723	6/25/85	JAPAN					
K.N.	AI	4-340717	11/27/92	JAPAN					
K.N.	AJ	2-94628	4/5/90	JAPAN	156	345			
K.N.	AK	1-14920	1/19/89	JAPAN	156	345			
K.N.	AL	1-32631	2/2/89	JAPAN	156	345			

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K.N.	AN	Y. Ra et al., J. Vac. Sci. Technol. 11(6) 2911 :Direct current bias...transformer coupled plasma etcher, 11/1993.
K.N.	AO	M.W. Horn et al., Optical Eng. 32(10) 2388 "Comparison of etching tools...", 10/1993.

EXAMINER  <i>Khennigyan</i>	DATE CONSIDERED  12/5/02
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
K.N.	AA	5,344,536	9/6/94	OBUCHI et al.	156	643	
K.N.	AB	5,156,703	10/20/92	OECHSNER	156	643	
K.N.	AC	5,183,777	2/2/93	DORI et al.	437	225	
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K.N.	AG	04-354124	12/8/92	JAPAN					
K.N.	AH	5-234955	9/10/93	JAPAN	216	70			
K.N.	AI	63-43324	2/24/88	JAPAN	156	345			
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K.N.	AM	"Charging Damage to Gate Oxides in a O <sub>2</sub> Magnetron Plasma", Fang et al., J. Appl. Phys., Vol. 72, No. 10, November 15, 1992, pgs 4865-4872.
K.N.	AN	H. Nihei et al., Rev. Sci. Instrum., 63 (3) March 1992, pgs. 1932, "...Plasma source using an axial mirror and multiple fields".
K.N.	AO	M. Shimada et al., J. Vac. Sci. Technol. A 11(11), July/August 1993, pg. 1313, "Compact ECR ion source with a permanent magnet".

EXAMINER  K. Himmigayen	DATE CONSIDERED  12/5/02
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EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
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K.N.	AM	K. Junck et al., J. Vac. Sci. Technol. A12(3), May/June 1994, pg760, "ECR plasmas in 3 magnetic field configurations"
K.N.	AN	V. Hashimoto, Japan J. Appl. Phys., 32 (1993) 6109, "Charge Damage in Plasma Etching...through Antenna".
K.N.	AO	S. Samukawa et al., J. Vac Sci. Technol, B93 (1991) 1471 "400 KMZ RF biased ECR plasma etching for ....."

EXAMINER

DATE CONSIDERED

K. Hennigsen

12/5/02

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